# **BOURNS®**

#### TISP4070L3AJ THRU TISP4395L3AJ

#### BIDIRECTIONAL THYRISTOR OVERVOLTAGE PROTECTORS

# **TISP4xxxL3AJ Overvoltage Protector Series**

#### SMA (DO-214AC) Package 25% Smaller Placement Area than SMB

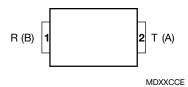
#### Ion-Implanted Breakdown Region Precise and Stable Voltage

Device	V <sub>DRM</sub>	V <sub>(BO)</sub>			
Device	V	V			
'4070	58	70			
'4080	65	80			
'4090	70	90			
'4125	100	125			
'4145	120	145			
'4165	135	165			
'4180	145	180			
'4220	160	220			
'4240	180	240			
'4260	200	260			
'4290	230	290			
'4320	240	320			
'4350	275	350			
'4360	290	360			
'4395	320	395			

#### **Rated for International Surge Wave Shapes**

Wave Shape	Standard	I <sub>TSP</sub>
wave Shape	Staridaid	Α
2/10 μs	GR-1089-CORE	125
8/20 μs	IEC 61000-4-5	100
10/160 μs	FCC Part 68	65
10/700 μs	ITU-T K.20/21/45	50
10/560 μs	FCC Part 68	40
10/1000 μs	GR-1089-CORE	30

#### SMAJ Package (Top View)



#### **Device Symbol**



Terminals T and R correspond to the alternative line designators of A and B

UL Recognized Components

#### **How to Order**

Device	Package	Carrier	Order As
TISP4xxxL3AJ	SMA (DO-214AC)	Embossed Tape Reel Pack	TISP4xxxL3AJR-S

Insert xxx value corresponding to protection voltages of 070, 080, 090, etc.

<sup>\*</sup>RoHS Directive 2002/95/EC Jan. 27, 2003 including annex and RoHS Recast 2011/65/EU June 8, 2011.

JULY 2000 - REVISED SEPTEMBER 2014

Specifications are subject to change without notice.

The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time. Users should verify actual device performance in their specific applications.

# TISP4xxxL3AJ Overvoltage Protector Series

### **BOURNS**®

#### Description

These devices are designed to limit overvoltages on the telephone line. Overvoltages are normally caused by a.c. power system or lightning flash disturbances which are induced or conducted on to the telephone line. A single device provides 2-point protection and is typically used for the protection of 2-wire telecommunication equipment (e.g. between the Ring and Tip wires for telephones and modems). Combinations of devices can be used for multi-point protection (e.g. 3-point protection between Ring, Tip and Ground).

The protector consists of a symmetrical voltage-triggered bidirectional thyristor. Overvoltages are initially clipped by breakdown clamping until the voltage rises to the breakover level, which causes the device to crowbar into a low-voltage on state. This low-voltage on state causes the current resulting from the overvoltage to be safely diverted through the device. The high crowbar holding current helps prevent d.c. latchup as the diverted current subsides.

The TISP4xxxL3 range consists of fifteen voltage variants to meet various maximum system voltage levels (58 V to 320 V). They are guaranteed to voltage limit and withstand the listed international lightning surges in both polarities. These protection devices are in an SMAJ (JEDEC DO-214AC with J-bend leads) plastic package. These devices are supplied in embossed tape reel carrier pack. For alternative voltage and holding current values, consult the factory. For higher rated impulse currents, the 50 A 10/1000 TISP4xxxM3AJ series in SMA and the 100 A 10/1000 TISP4xxxH3BJ series in SMB are available.

#### Absolute Maximum Ratings, T<sub>A</sub> = 25 °C (Unless Otherwise Noted)

Rating	Symbol	Value	Unit
'407	0	± 58	
'408	30	± 65	
'409	00	± 70	
'412	25	±100	
'414	<b>5</b>	±120	
'416	55	±135	
'418	30	±145	
Repetitive peak off-state voltage, (see Note 1) '422	0 V <sub>DRM</sub>	±160	V
·424		±180	
·426	60	±200	
'429	00	±230	
'432	20	±240	
·435	50	±275	
'436	60	±290	
'439	95	±320	
Non-repetitive peak on-state pulse current (see Notes 2, 3 and 4)			
2/10 μs (GR-1089-CORE, 2/10 μs voltage wave shape)		125	
8/20 μs (IEC 61000-4-5, combination wave generator, 1.2/50 voltage, 8/20 current)		100	
10/160 μs (FCC Part 68, 10/160 μs voltage wave shape)		65	
5/310 μs (ITU-T K.20/21/45, K.44 10/700 μs voltage wave shape)	I <sub>TSP</sub>	50	Α
5/310 µs (FTZ R12, 10/700 µs voltage wave shape)		50	
10/560 μs (FCC Part 68, 10/560 μs voltage wave shape)		40	
10/1000 μs (GR-1089-CORE, 10/1000 μs voltage wave shape)		30	
Non-repetitive peak on-state current (see Notes 2, 3 and 4)			
20 ms (50 Hz) full sine wave		18	
1 s (50 Hz) full sine wave	I <sub>TSM</sub>	7	Α
1000 s 50 Hz/60 Hz a.c.		1.6	
Junction temperature	TJ	-40 to +150	°C
Storage temperature range	T <sub>stg</sub>	-65 to +150	°C

NOTES: 1. For voltage values at lower temperatures, derate at 0.13 %/°C.

- 2. Initially, the TISP4xxxL3 must be in thermal equilibrium with  $T_{II} = 25$  °C.
- 3. The surge may be repeated after the TISP4xxxL3 returns to its initial conditions.
- EIA/JESD51-2 environment and EIA/JESD51-3 PCB with standard footprint dimensions connected with 5 A rated printed wiring track widths. Derate current values at -0.61 %°C for ambient temperatures above 25 °C.

#### **Recommended Operating Conditions**

	Component			Max	Unit
	series resistor for FCC Part 68, 10/560 type A surge survival				Ω
	series resistor for FCC Part 68, 9/720 type B surge survival	0			Ω
$R_S$	series resistor for GR-1089-CORE first-level and second-level surge survival	23			Ω
	series resistor for K.20, K.21 and K.45 1.5 kV, 10/700 surge survival	0			Ω
	series resistor for K.20, K.21 and K.45 coordination with a 400 V primary protector	7			Ω

#### Electrical Characteristics, T<sub>A</sub> = 25 °C (Unless Otherwise Noted)

	Parameter	Test Conditions		Min	Тур	Max	Unit
loou	Repetitive peak off-	$V_D = V_{DRM}$	T <sub>A</sub> = 25 °C			±5	μΑ
I <sub>DRM</sub>	state current	VD - VDRM	$T_A = 85  ^{\circ}C$			±10	μΛ
			'4070			±70	
1			'4080			±80	
1			'4090			±90	
1		'412	'4125			±125	
1			'4145			±145	
			'4165			±165	
			'4180			±180	
V <sub>(BO)</sub>	Breakover voltage	dv/dt = $\acute{A}$ G50 V/ms, R <sub>SOURCE</sub> = 300 $\Omega$	'4220			±220	V
			'4240			±240	
			'4260			±260	
1			'4290			±290	
			'4320			±320	
			'4350			±350	
			'4360			±360	
			'4395			±395	
I <sub>(BO)</sub>	Breakover current	$dv/dt = \pm G = 0 \text{ V/ms}, \qquad R_{SOURCE} = 300 \Omega$				±0.İ	Α
lΗ	Holding current	$I_T = \pm 5 \text{ A, di/dt} = \pm -30 \text{ mA/ms}$		±0.15		±0.60	Α
dv/dt	Critical rate of rise of off-state voltage	Linear voltage ramp, Maximum ramp value < 0.85V <sub>DRM</sub>		±5			kV/μs
	<u> </u>	'4070, V <sub>D</sub> = ± 52V					
		'4080, $V_D = \pm 59V$					
		'4090, $V_D = \pm 63V$					
		$^{4}125, V_{D} = \pm 90 V$					
		$^{4145}$ , $V_D = \pm 108 \text{ V}$					
1		'4165, $V_D = \pm 122 \text{ V}$					
		'4180, $V_D = \pm 131 \text{ V}$					
ID	Off-state current	$^{4220}$ , $V_{D} = \pm 144 \text{ V}$				±2	μΑ
		$^{4240}$ , $V_D = \pm 162 \text{ V}$					
		'4260, $V_D = \pm 180 \text{ V}$					
1		'4290, V <sub>D</sub> = ±207 V					
		'4320, V <sub>D</sub> = ±216 V					
		$^{4}350, V_D = \pm 248 \text{ V}$					
l		'4360, V <sub>D</sub> = ±261 V					
		'4395, V <sub>D</sub> = ±288 V					
	Off-state current	$V_D = \pm 50 \text{ V}$				±10	μΑ

# **TISP4xxxL3AJ Overvoltage Protector Series**

#### Electrical Characteristics, T<sub>A</sub> = 25 °C (Unless Otherwise Noted) (Continued)

	Parameter		Test Conditions		Min	Тур	Max	Unit
		$f = 1 \text{ MHz}, V_0$	$V_{\rm d} = 1 \text{ V rms}, V_{\rm D} = \pm 1 \text{ V}$	4070 thru '4090		53	64	
				'4125 thru '4220		40	48	
C	Off state conscitance			'4240 thru '4395		33	40	рF
C <sub>off</sub>	Off-state capacitance	$f = 1 \text{ MHz}, V_0$	$V_{\rm d} = 1 \text{ V rms}, V_{\rm D} = \pm 50 \text{ V}$	'4070 thru '4090		25	30	рг
				'4125 thru '4220		18	22	
				'4240 thru '4395		14	17	

#### **Thermal Characteristics**

	Parameter	Test Conditions	Min	Тур	Max	Unit
$R_{\theta JA}$	Junction to free air thermal resistance	EIA/JESD51-3 PCB, $I_T = I_{TSM(1000)}$ , $T_A = 25$ °C, (see Note 75)			115	°C/W
Т	various to not an infermal resistance	265 mm x 210 mm populated line card, 4-layer PCB, I <sub>T</sub> = I <sub>TSM(1000)</sub> , T <sub>A</sub> = 25 °C		52		O/VV

NOTE 5: EIA/JESD51-2 environment and PCB has standard footprint dimensions connected with 5 A rated printed wiring track widths.

#### **Parameter Measurement Information**

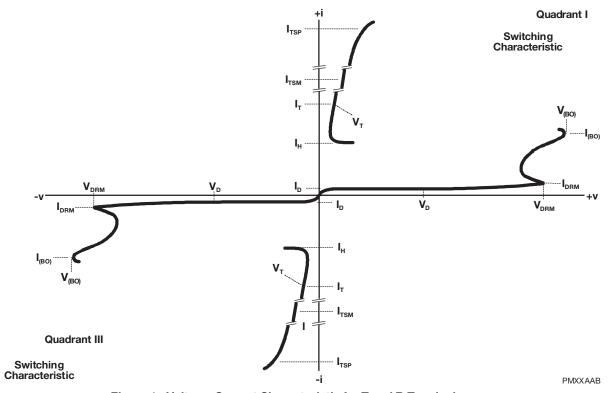


Figure 1. Voltage-Current Characteristic for T and R Terminals All Measurements are Referenced to the R Terminal

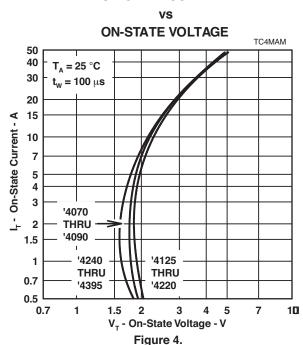
#### **Typical Characteristics**

# OFF-STATE CURRENT VS JUNCTION TEMPERATURE TC4LAG TC4LAG O-001 -25 0 25 50 75 100 125 150

Figure 2.

#### **ON-STATE CURRENT**

T, - Junction Temperature - °C



#### NORMALIZED BREAKOVER VOLTAGE

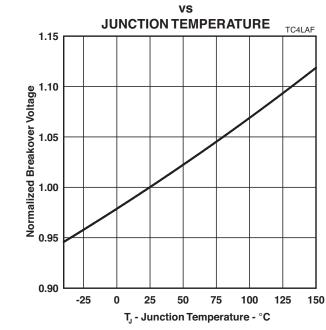
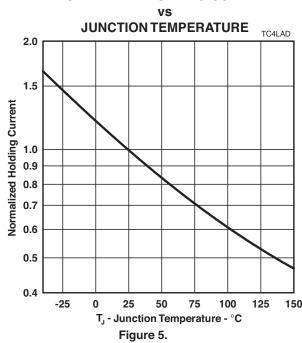


Figure 3.

#### NORMALIZED HOLDING CURRENT



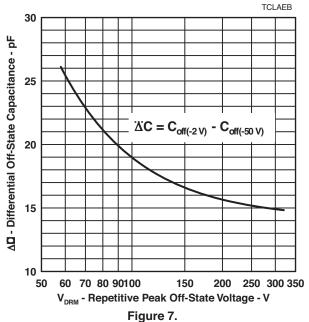
#### **Typical Characteristics**

#### **NORMALIZED CAPACITANCE**

#### **OFF-STATE VOLTAGE** TC4LABC 0.9 $T_{J} = 25 \, ^{\circ}C$ 0.8 $V_d = 1 \text{ Vrms}$ Capacitance Normalized to $V_D = 0$ 0.7 0.6 0.5 '4070 THRU '4090 0.4 '4125 THRU '4220 0.3 '4240 THRU '4395 0.2 0.5 1 10 20 30 100150 V<sub>D</sub> - Off-state Voltage - V Figure 6.

#### **DIFFERENTIAL OFF-STATE CAPACITANCE**

#### RATED REPETITIVE PEAK OFF-STATE VOLTAGE



#### TYPICAL CAPACITANCE ASYMMETRY

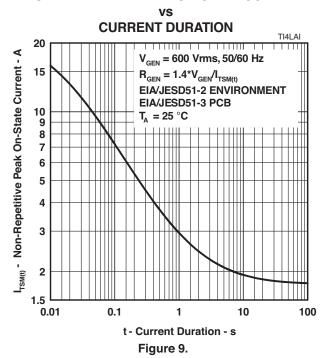
**OFF-STATE VOLTAGE** TC4LBB  $V_d = 10 \text{ mV rms}, 1 \text{ MHz}$ IC<sub>off(+VD)</sub>- C<sub>off(vD)</sub> I — Capacitance Asymmetry —  $V_d = 1 \text{ Vrm s}, 1 \text{ MHz}$ 0 4 5 7 10 1 2 20 30 40 50 Off-state Voltage - V

Figure 6.

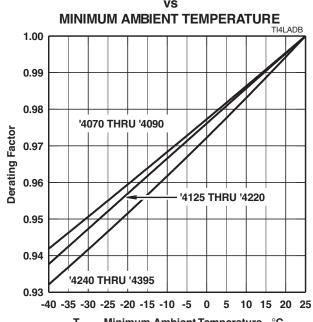
# TISP4xxxL3AJ Overvoltage Protector Series

#### **Rating and Thermal Information**

#### NON-REPETITIVE PEAK ON-STATE CURRENT

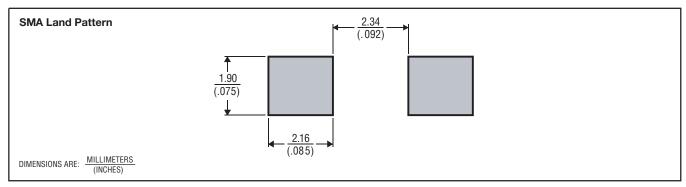


#### **V<sub>DRM</sub> DERATING FACTOR**



#### **MECHANICAL DATA**

#### **Recommended Printed Wiring Land Pattern Dimensions**



**MDXXBIC** 

#### **Device Symbolization Code**

Devices will be coded as below. As the device parameters are symmetrical, terminal 1 is not identified.

Device	Symbolization
Device	Code
TISP4070L3	4070L
TISP4080L3	4080L
TISP4090L3	4090L
TISP4125L3	4125L
TISP4145L3	4145L
TISP4165L3	4165L
TISP4180L3	4180L
TISP4220L3	4220L
TISP4240L3	4240L
TISP4260L3	4260L
TISP4290L3	4290L
TISP4320L3	4320L
TISP4350L3	4350L
TISP4360L3	4360L
TISP4395L3	4395L

#### **Carrier Information**

For production quantities, the carrier will be embossed tape reel pack. Evaluation quantities may be shipped in bulk pack or embossed tape.

Carrier	Standard Quantity
Embossed Tape Reel Pack	5,000

<sup>&</sup>quot;TISP" is a trademark of Bourns, Ltd., a Bourns Company and is registered in the U.S. Patent and Trademark Office. "Bourns" is a registered trademark of Bourns, Inc. in the U.S. and other countries.

JULY 2000 - REVISED SEPTEMBER 2014

 $<sup>\</sup>underline{\underline{S}} pecifications \ are \ subject \ to \ change \ without \ notice.$ 

The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time. Users should verify actual device performance in their specific applications.

## **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

#### Bourns:

<u>TISP4240L3AJR-S</u> <u>TISP4290L3AJR-S</u> <u>TISP4180L3AJR-S</u> <u>TISP4145L3AJR-S</u> <u>TISP4165L3AJR-S</u> <u>TISP4125L3AJR-S</u> <u>TISP4220L3AJR-S</u> <u>TISP4260L3AJR-S</u> <u>TISP4395L3AJR-S</u> <u>TISP4080L3AJR-S</u> <u>TISP4090L3AJR-S</u> S TISP4070L3AJR-S TISP4320L3AJR-S TISP4360L3AJR-S TISP4350L3AJR-S